

HiPerFRED

$$V_{RRM} = 600 \text{ V}$$

$$I_{FAV} = 6 \text{ A}$$

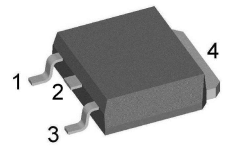
$$t_{rr} = 20 \text{ ns}$$

High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 Single Diode

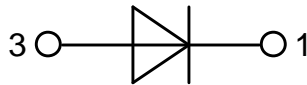
Part number

DSEP6-06AS

Marking on Product: 6P060AS



Backside: cathode

**Features / Advantages:**

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-252 (DPak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

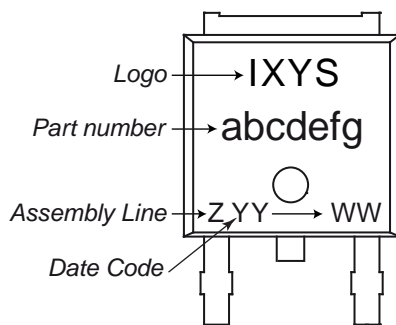
- to perform joint risk and quality assessments;

- the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

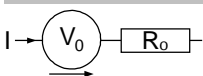
Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage					600	V
V_{RRM}	max. repetitive reverse blocking voltage					600	V
I_R	reverse current, drain current	$V_R = 600\text{ V}$		$T_{VJ} = 25^\circ\text{C}$		50	μA
		$V_R = 600\text{ V}$		$T_{VJ} = 150^\circ\text{C}$		0.2	mA
V_F	forward voltage drop	$I_F = 6\text{ A}$		$T_{VJ} = 25^\circ\text{C}$		2.03	V
		$I_F = 12\text{ A}$				2.22	V
		$I_F = 6\text{ A}$		$T_{VJ} = 150^\circ\text{C}$		1.34	V
		$I_F = 12\text{ A}$				1.55	V
I_{FAV}	average forward current	$T_C = 150^\circ\text{C}$	rectangular	$T_{VJ} = 175^\circ\text{C}$		6	A
V_{FO}	threshold voltage			$T_{VJ} = 175^\circ\text{C}$		1.00	V
r_F	slope resistance	} for power loss calculation only				34	m Ω
R_{thJC}	thermal resistance junction to case					2.8	K/W
R_{thCH}	thermal resistance case to heatsink				0.50		K/W
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$		55	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$		$T_{VJ} = 45^\circ\text{C}$		40	A
C_J	junction capacitance	$V_R = 400\text{ V}$ $f = 1\text{ MHz}$		$T_{VJ} = 25^\circ\text{C}$		5	pF
I_{RM}	max. reverse recovery current			$T_{VJ} = 25^\circ\text{C}$		3	A
t_{rr}	reverse recovery time	} $I_F = 6\text{ A}; V_R = 300\text{ V}$ $-di_F/dt = 200\text{ A}/\mu\text{s}$		$T_{VJ} = 100^\circ\text{C}$		5	A
				$T_{VJ} = 25^\circ\text{C}$		20	ns
				$T_{VJ} = 100^\circ\text{C}$		80	ns

Package TO-252 (DPak)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			20	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				0.3		g
F_C	mounting force with clip		20		60	N

Product Marking


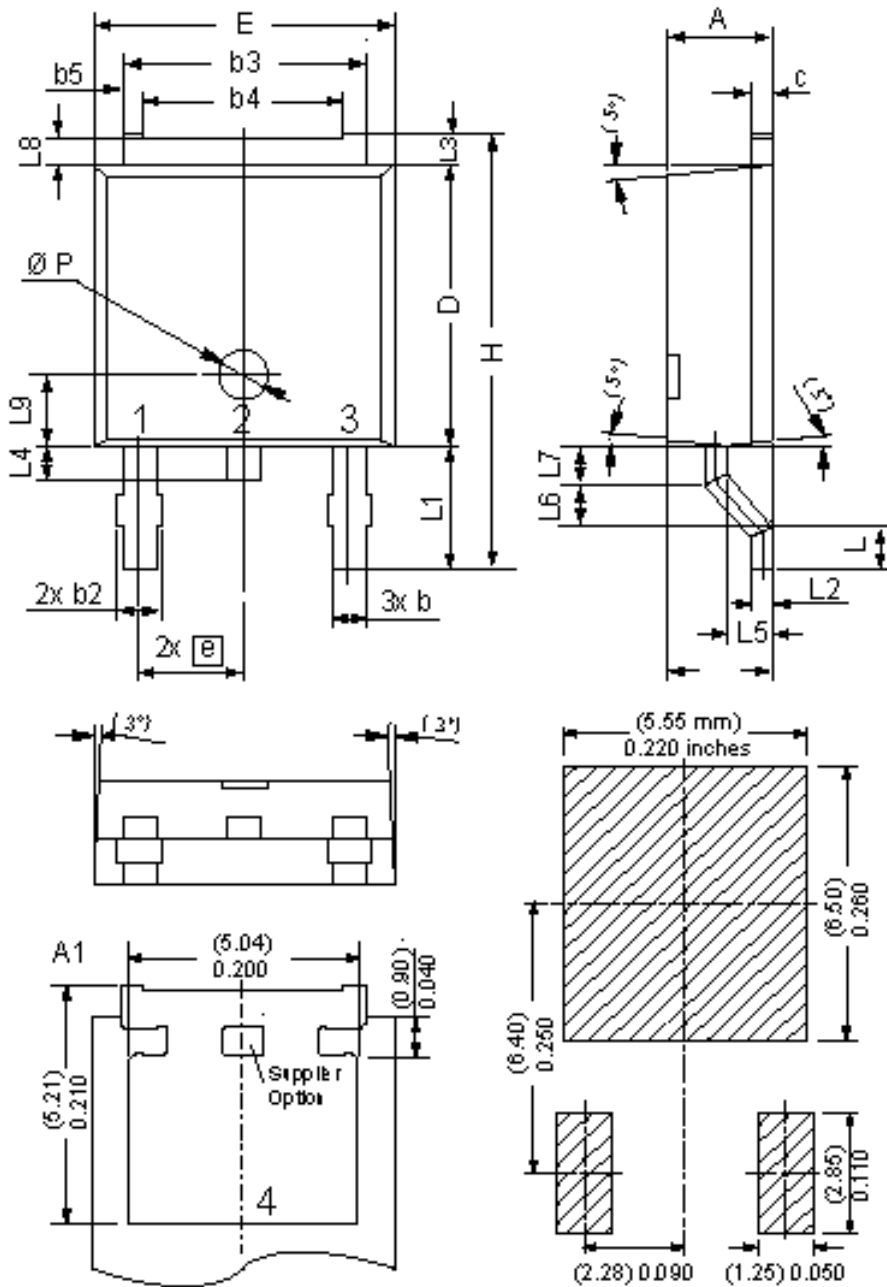
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEP6-06AS	6P060AS	Tape & Reel	2500	509806

Similar Part	Package	Voltage class
DSEP6-06BS	TO-252AA (DPak)	600

Equivalent Circuits for Simulation
** on die level*
 $T_{VJ} = 175\text{ °C}$

Fast Diode

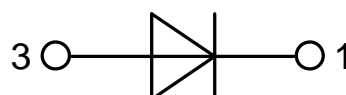
$V_{0\ max}$	threshold voltage	1	V
$R_{0\ max}$	slope resistance *	30	mΩ

Outlines TO-252 (DPak)



Dim	Millimeters		Inches	
	min	max	min	max
A	2.20	2.40	0.087	0.094
A1	2.10	2.50	0.083	0.098
b	0.66	0.86	0.026	0.034
b2	-	0.96	-	0.038
b3	5.04	5.64	0.198	0.222
b4	4.34	BSC	0.171	BSC
b5	0.50	BSC	0.020	BSC
c	0.40	0.86	0.016	0.034
D	5.90	6.30	0.232	0.248
E	6.40	6.80	0.252	0.268
e	2.10	2.50	0.083	0.098
H	9.20	10.10	0.362	0.398
L	0.55	1.28	0.022	0.050
L1	2.50	2.90	0.098	0.114
L2	0.40	0.60	0.016	0.024
L3	0.50	0.90	0.020	0.035
L4	0.60	1.00	0.024	0.039
L5	0.82	1.22	0.032	0.048
L6	0.79	0.99	0.031	0.039
L7	0.81	1.01	0.032	0.040
L8	0.40	0.80	0.016	0.031
L9	1.50	BSC	0.059	BSC
Ø P	1.00	BSC	0.039	BSC

Recommended
min. footprint



Fast Diode

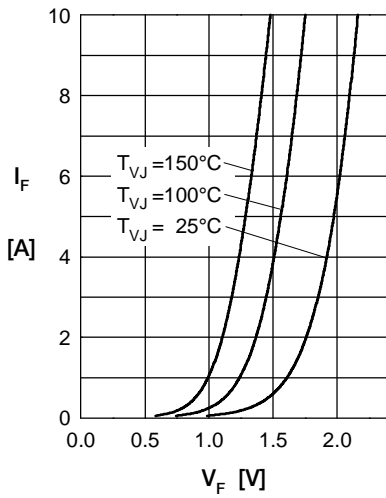


Fig. 1 Forward current I_F versus V_F

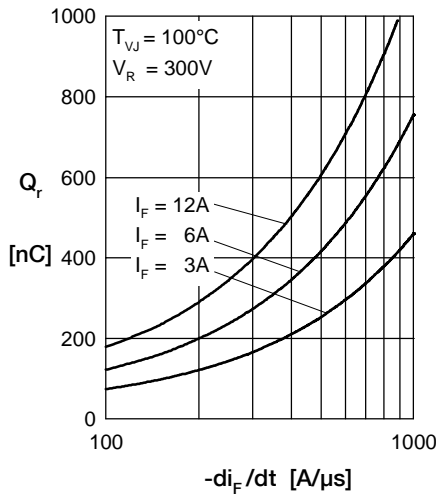


Fig. 2 Typ. reverse recov. charge Q_r versus $-di_F/dt$

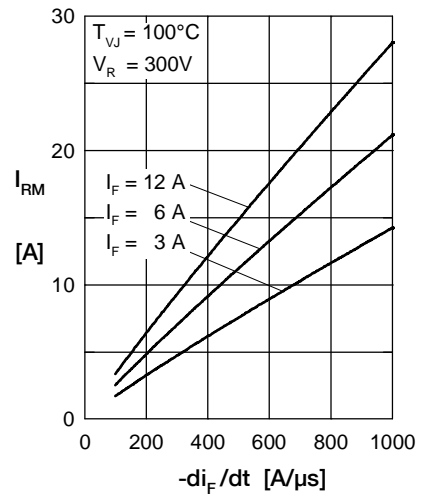


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

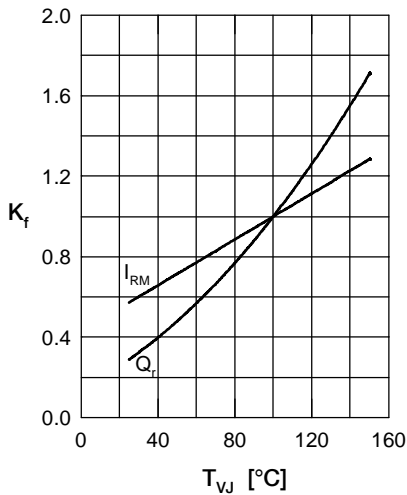


Fig. 4 Typ. dynamic parameters Q_r , I_{RM} versus T_{VJ}

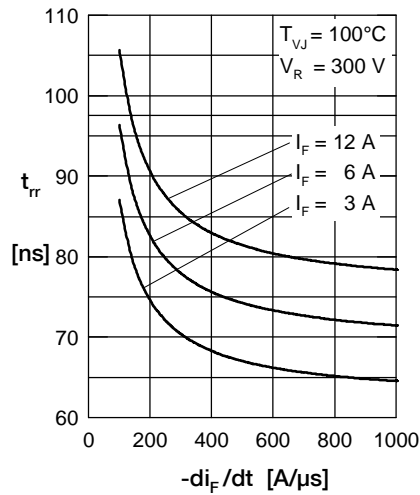


Fig. 5 Recovery time t_{rr} versus $-di_F/dt$

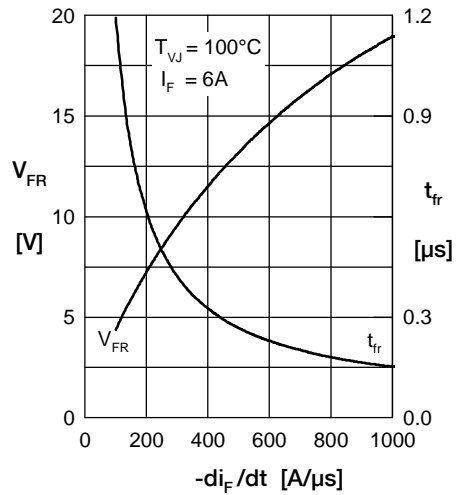


Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt

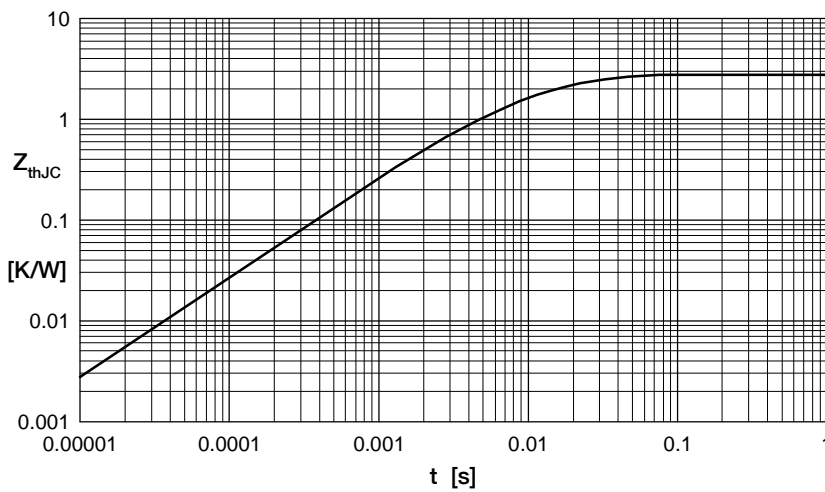


Fig. 7 Transient thermal resistance junction to case

Mouser Electronics

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